

ATTACHMENT

39. (Amended) A device according to claim 38, wherein said process comprises:
growing said first buffer layer at a temperature between 350° C and 800° C.

51. (Amended) A semiconductor device comprising:

a substrate;

crystals formed on said substrate and containing at least Al and N, said crystals

having intervals therebetween so as to expose said substrate;

a thermal distortion reducing layer made of $\text{Al}_{1-u-v}\text{Ga}_u\text{In}_v\text{N}$ ($0 \leq u < 1, 0 \leq v < 1, u+v < 1$)
 $0 \leq u \leq 1, 0 \leq v \leq 1, u+v \leq 1$) formed on said crystals and having a different chemical formula from
that of said crystals;

a first cladding layer formed over said thermal distortion reducing layer;

an active layer formed on said first cladding layer; and

a second cladding layer formed on said active layer.

78. (Amended) A semiconductor device according to claim 76, wherein a film
thickness of said thermal distortion reducing layer is greater than that of said buffer
semiconductor layer.

83. (Amended) A semiconductor device according to claim 76, further comprising a
single crystal substrate on which said buffer semiconductor layer is formed.

87. (Amended) The semiconductor device according to claim 76, wherein:
said buffer semiconductor layer consists essentially of an AlGa_xN material.

88. (Amended) The semiconductor device according to claim 76, wherein:
said buffer semiconductor layer consists essentially of an AlN material.

89. (Amended) The semiconductor device according to claim 76, wherein:
said thermal distortion reducing layer consists essentially of a GaN material.